Infrared Emitting Diode(GaAs)

KODENSHI

EL333

The EL333 is a Double-end Type IR Emtting Diode mounted in a compact clear package.
EL333 is compact size and easy to mount on small space.

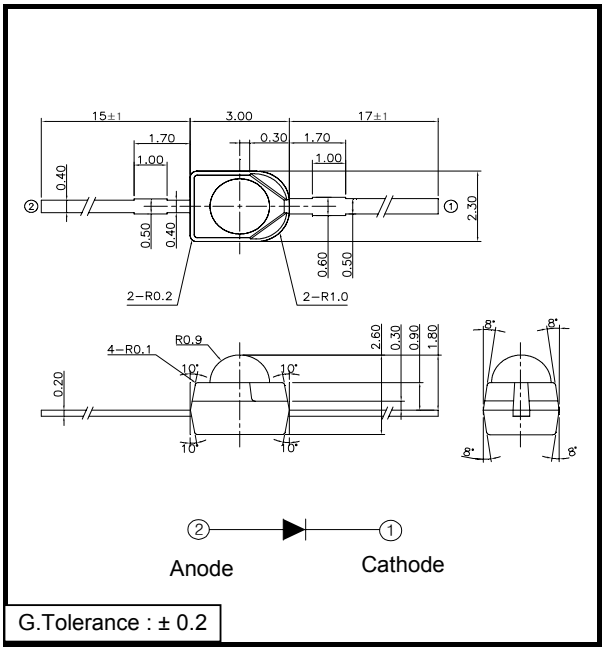
Features

- Compact package with double-end leads
- Clear plastic package
- RoHS Compliant

Applications

- Photointerrupter
- Optical switches
- Transmission sensor

Dimensions [Unit : mm]



Absolute Maximum Ratings [Ta = 25°C]

Parameter	Symbol	Rating	Unit
Forward Current	I_F	50	mA
Reverse Voltage	V_R	5	V
Pulse Forward Current*1	I_{FP}	1	A
Power Dissipation	P_D	75	mW
Operating Temperature	Topr.	-25~ + 85	°C
Storage Temperature	Tstg.	-30~ + 80	°C
Soldering Temperature*2	Tsol	260	°C

*1. Pulse width tw=100μsec, cycle T=10msec

*2. Distance from end of the package =2mm, time=5sec, Max.

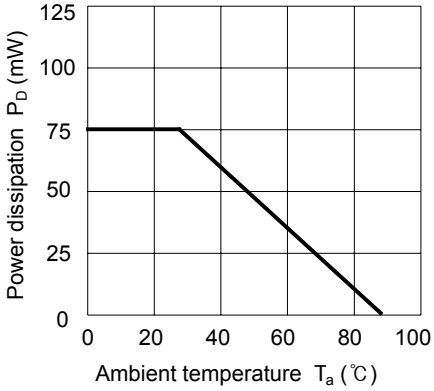
Electro-Optical Characteristics [Ta = 25°C]

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward Voltage	V_F	I_F=50mA	-	1.2	1.5	V
Reverse Current	I_R	V_R=5V	-	-	10	μA
Capacitance	C_T	f=1MHz	-	25	-	pF
Radiant intensity	P_O	I_F=20mA	0.8	-	-	mV
Peak Wavelength	λp	I_F=20mA	-	940	-	nm
Spectral Width at FWHM	Δλ	I_F=20mA	-	50	-	nm
Half Angle	ΔΘ		-	± 20	-	degrees

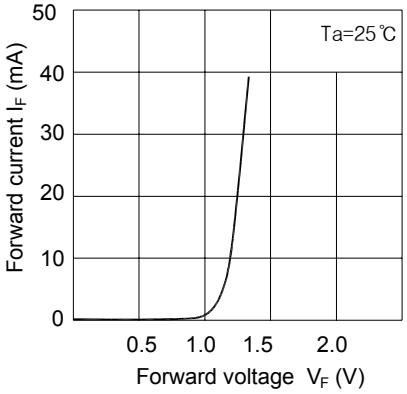
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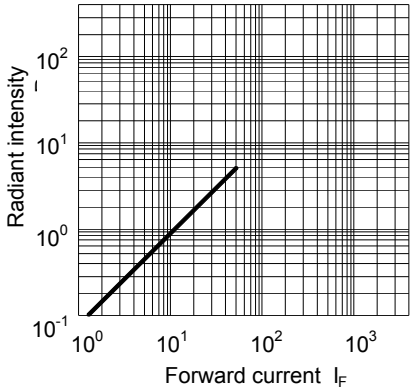
Power dissipation Vs. Ambient temperature



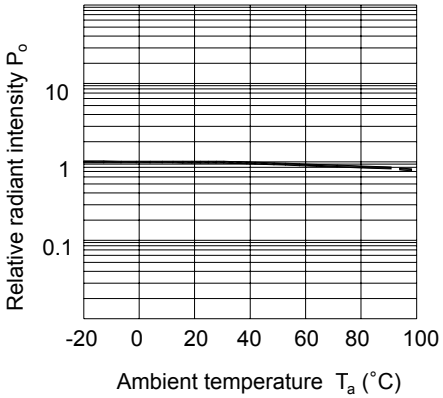
Forward current Vs. Forward voltage



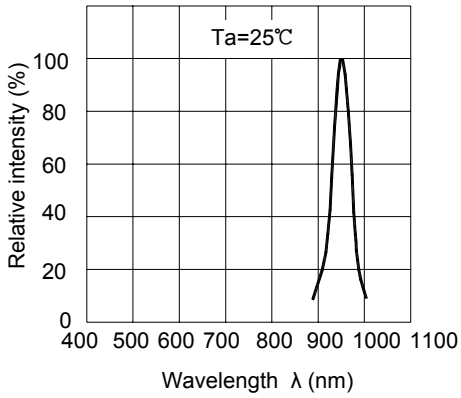
Radiant intensity Vs. Forwardb current



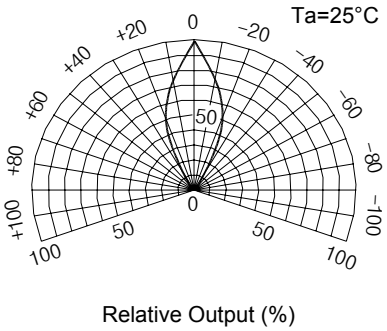
Realtive radiant intensity Vs. Ambient temperature



Relative intensity Vs. Wavelength



Sensitivity Diagram Angular Displacement



Relative Radiant intensity Vs. Distance

